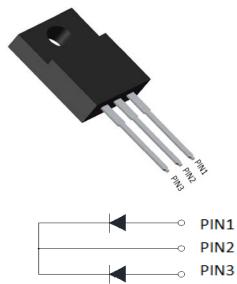


Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: ITO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102 • Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR1060FCTS	
Device marking code			MBR1060FCTS	
Repetitive Peak Reverse Voltage	VRRM	V	60	
Average Rectified Output Current @60Hz sine wave, R-load, Tc=120°C	Ю	Α	10	
Surge(Non-repetitive)Forward Current	IFSM	Α	400	
@60H _Z half sine-wave,1 cycle, T _a =25°C	IFOIVI	Α	100	
Current Squared Time @1ms≤t≤8.3ms	l ² t	A ² s	44	
Tj=25℃,	1.0	Α 5	41	
Storage Temperature	T _{stg}	°C	-55 ~ + 150	
Junction Temperature	Tj	°C	-55 ~ + 150	

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

			•	
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR1060FCTS
Maximum instantaneous forward voltage drop per diode	VFM	٧	IFM=5.0A	0.75
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM T _a =25°C	0.2
	IRRM2		VRM=VRRM T _a =125°C	50

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER		SYMBOL	UNIT	MBR1060FCTS
Thermal Resistance	Between junction and case	R ₀ J-C	W)°	4.0

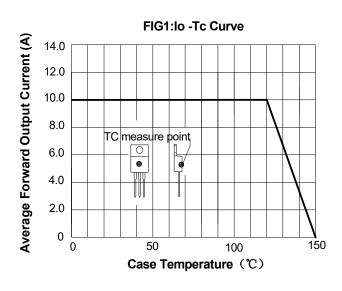
■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR1060FCTS	Approximate 1.6	50	1000	5000	Tube

Peak Forward Surge Current (A)

20

■Characteristics (Typical)



140
120
100
8.3ms Single
Half Sine-Wave
JEDEC Method
60
40

Number of Cycles

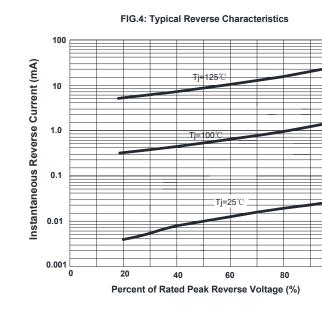
50

100

FIG2:Surge Forward Current Capability

FIG3: Forward Voltage

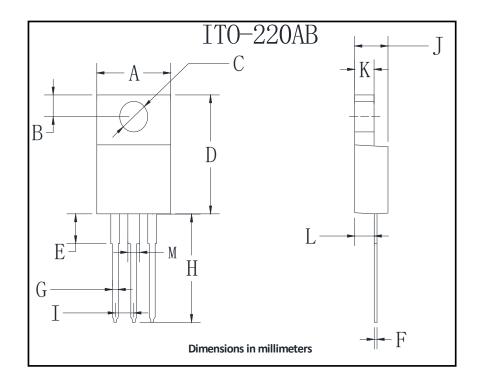
100
20
10
10
50
20
10
10
0.5
0.5
0.5
0.1
0.1
0.2
0.3
0.4
0.5
0.6
0.7
0.8
0.9
1.0
1.1
1.2
Instantaneous Forward Voltage (V)



100



■Outline Dimensions



ITO-220AB				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
Е	3.05	3.95		
F	0.45	0.75		
G	0.45	0.75		
Н	13.4	14.2		
I	2.35	2.75		
J	4.3	4.8		
K	2.58	2.82		
L	2.58	2.82		
М	1.47	1.77		



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